

Rev 1.0 27/12/22

#### Ultra-Fast recovery rectifier diode in bare die form

#### Features:

- Low leakage current
- High forward surge current capability
- Low forward voltage drop
- Robust construction
- High reliability tested grades.

### **Ordering Information**

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

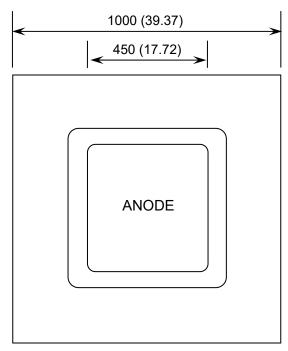
For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

### Supply Formats:

- Default Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- With additional electrical selection By specific request

#### Die Dimensions in µm (mils)



CHIP BACKSIDE IS CATHODE



### **Mechanical Specification**

Die Size (Unsawn)	1000 x 1000 39.37 x 39.37	µm mils	
Anode Pad Size	450 x 450 17.72 x 17.72	μm mils	
Die Thickness	220 (±20) 8.66 (±0.79)	μm mils	
Top Metal Composition	Al 7.5µm		
Back Metal Composition	Ti/Ni/Ag		





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### Absolute Maximum Ratings<sup>1</sup> T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT	
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>		V	
Working Peak Repetitive Reverse Voltage	V <sub>RWM</sub>	600		
DC Blocking Voltage	V <sub>R</sub>			
RMS Reverse Voltage	V <sub>R (RMS)</sub>	420	V	
Average Forward Rectified Current,	I <sub>F(AV)</sub>	1	A	
Non-Repetitive Peak Forward Surge Current <sup>3</sup>	I <sub>FSM</sub>	35	А	
Operating Junction temperature	TJ	-65 to 175	°C	
Storage Temperature Range	T <sub>STG</sub>	-65 to 175	°C	

### Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Instantaneous Forward Voltage <sup>4</sup>	VF	I <sub>F</sub> = 1A, T <sub>J</sub> = 25°C	-	1.10	1.25	V
	V F	I <sub>F</sub> = 1A, T <sub>J</sub> = 150°C	-	-	1.05	<b>V</b>
Maximum Instantaneous Reverse Leakage Current <sup>4</sup> I <sub>RM</sub> @ V	I <sub>RM</sub> @ V <sub>RRM</sub>	V <sub>RRM</sub> = 600V, T <sub>J</sub> = 25°C	-	0.02	1	μA
	IRM W VRRM	V <sub>RRM</sub> = 600V, T <sub>J</sub> = 150°C	-	-	150	μ/ (
Reverse Recovery Time	t <sub>rr</sub>	$I_F = 0.5A$ , $I_R = 1.0A$ , $I_{rr} = 0.25A$	-	-	50	ns
Junction Capacitance	CJ	V <sub>R</sub> = 4V, f = 1.0MHz	-	15	-	pF

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. V<sub>R</sub> = 600V, Square Wave, 20kHz Pulse Width = 3.8ms 3. Assembled in SOD-123F, surge applied at rated load conditions halfwave, single phase, 60Hz, die form requires heat sinking 4. Pulse Test: Pulse Width = 300s, Duty Cycle ≤ 2.0%

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

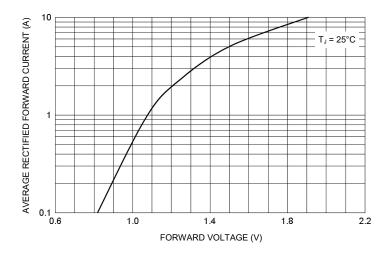


FIGURE 1. Forward Voltage Characteristics





Typical Characteristics Continued T<sub>J</sub> = 25°C unless otherwise stated

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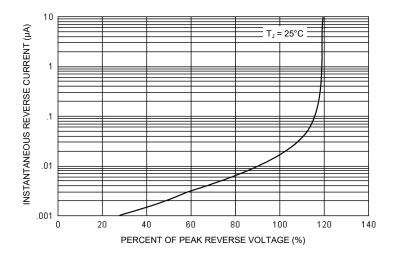


FIGURE 2. Reverse Current Versus Reverse Voltage

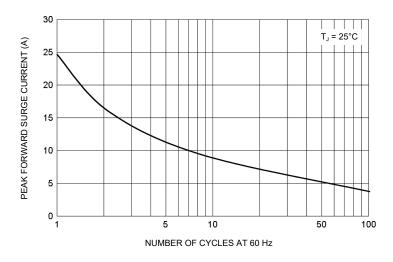


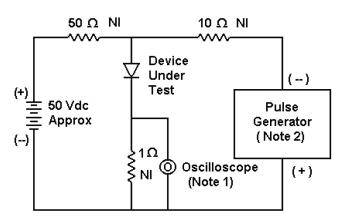
FIGURE 3. Peak Forward Surge Current Versus Cycles at 60 Hz

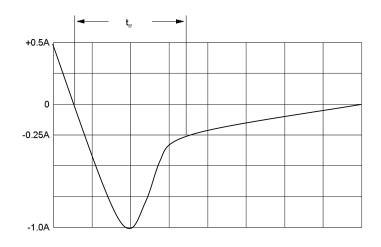




### Typical Characteristics Continued T<sub>J</sub> = 25°C unless otherwise stated

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#### Notes:

- 1. Rise Time = 7 ns max. Input Impedance =1 M  $\Omega$  , 22 pF
- 2. Rise Time = 10 ns max. Input Impedance =  $50 \Omega$

Set time base for 10/20 ns/cm



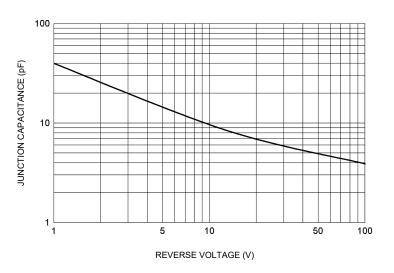


FIGURE 5. Typical Junction Capacitance

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